

Silicon NPN Epitaxial Type Transistor

Features

• High DC current gain:hFE=200TYP

(VCE=6.0V,IC=1.0mA).

- High Voltage:VCEO=50V
- RoHS compliant package

Applications

NPN Silicon Epitaxial Planar Transistor.

Audio frequency general purpose amplifier.

Mechanical Data

Case: SOT-23 Molded plastic

Packing & Order Information

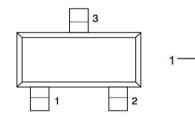
3,000/Reel

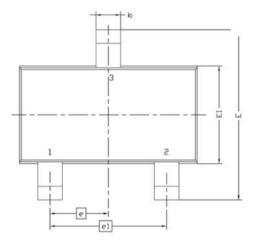


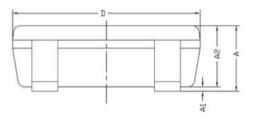


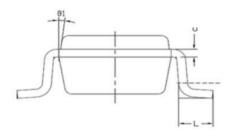
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Graphic symbol









Cumbal	MILLIMETERS		
Symbol	MIN	MAX	
Α	0.8	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7		
E	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
L	0.3	0.6	
θ1	7° NOM		



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATING @ Ta=25°C unless otherwise specified					
Symbol	Parameter	Value	Unit		
V _{CBO}	Collector-Base Voltage	60	V		
V _{CEO}	Collector-Emitter Voltage	50	V		
V _{EBO}	Emitter-Base Voltage	5	V		
Ic	Collector Current	100	mA		
P _C	Collector Dissipation	200	mW		
Tj,Tstg	Junction and Storage Temperature	-55 to +150	°C		

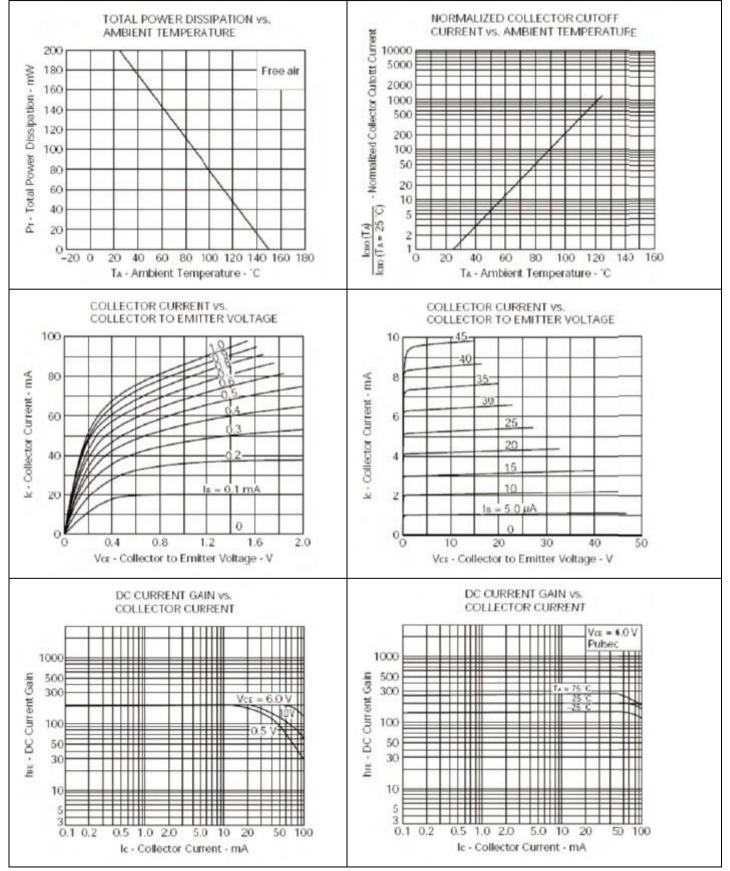
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified						
Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	$I_{C} = 100 \mu A$, $I_{E} = 0$ 6				v
V _(BR) CEO	Collector-emitter breakdown voltage	$I_C = 1 mA , I_B = 0 \qquad \qquad 5$				V
V(BR)EBO	Emitter-base breakdown voltage	$I_E=100 \mu A$, $I_C=0$	5			v
I _{CBO}	Collector cut-off current	$V_{CB}=60\ V$, $I_{E}=0$				uA
Іево	Emitter cut-off current	$V_{EB}=5\ V\ ,\ I_C=0$				uA
hfe	DC current gain	$V_{CE} = 6 V$, $I_C = 1 mA$	90	200	600	
VCE(sat)	Collector-emitter saturation voltage	$I_C = 100 mA , I_B = 10 mA$		0.15	0.3	v
V _{BE(sat)}	Base-emitter saturation voltage	$I_{\rm C} = 100 {\rm mA}$, $I_{\rm B} = 10 {\rm mA}$		0.86	1.0	V
V _{BE}	Base Emitter Voltage	$V_{CE} = 6 V$, $I_C = 1 mA$	0.55	0.62	0.65	V
fT	Transition frequency	$V_{CE} = 6 V$, $I_E = -10 mA$		250		MHz
C _{ob}	Output capacitance	$V_{CB} = 6 \ V \ , \ I_E = 0 \ \label{eq:CB}$ $f = 1.0 MHz$		3.0		pF

CLASSIFICATION OF hFE(1)					
Rank	L4	L5	L6	L7	
Range	90-180	135-270	200-400	300-600	
Marking	L4	L5	L6	L7	



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RATINGS AND CHARACTERISTIC CURVES





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